

BULD742C

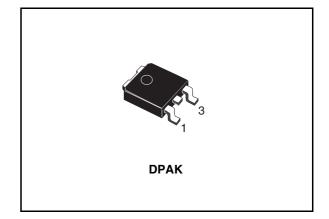
High voltage fast-switching NPN power transistor

Features

- Low spread of dynamic parameters
- High voltage capability
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

Applications

- Electronic ballast for fluorescent lighting
- Switch mode power supplies



Description

The device is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and high voltage capability. Thanks to an increased intermediate layer, it has an intrinsic ruggedness which enables the transistor to withstand an high collector current level during breakdown condition, without using the transil protection usually necessary in typical converters for lamp ballast.

Figure 1. Internal schematic diagram

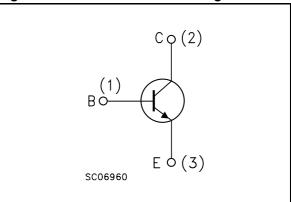


Table 1. Device summary

Order code Marking		Package	Packaging	
BULD742CT4	BULD742C	DPAK	Tape & reel	

Contents BULD742C

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BULD742C Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	1050	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	400	V
V _{EBO}	Emitter-base voltage ($I_C = 0$, $I_B = 2$ A, $t_p < 10$ ms)	V _{(BR)EBO}	V
I _C	Collector current	4	Α
I _{CM}	Collector peak current (t _P < 5ms)	8	Α
I _B	Base current	2	Α
I _{BM}	Base peak current (t _P < 5ms)	4	Α
P _{tot} Total dissipation at T _c = 25°C		45	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction - case	2.78	°C/W
R _{thj-amb}	Thermal resistance junction - ambient	73	°C/W

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Electrical characteristics BULD742C

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 4. Electrical characteristics

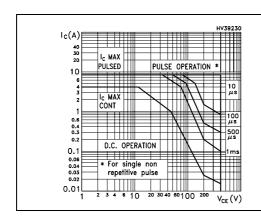
Symbol	Parameter	Test Conditions		Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	V _{CE} =1050 V		0.2	10	μА
I _{CEO}	Collector cut-off current (I _B = 0)	V _{CE} =400 V		10	250	μА
V _{(BR)EBO}	Emitter base breakdown voltage (I _C = 0)	I _E = 1 mA	15	19	24	V
V _{CEO(sus)} (1)	Collector-emitter sustaining voltage (I _B = 0)	I _C =10 mA	400	450		V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 1 \text{ A}$ $I_B = 0.2 \text{ A}$ $I_C = 3.5 \text{ A}$ $I_B = 1 \text{ A}$		0.15 0.6	0.5 1.5	V V
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C = 3.5 A I _B = 1 A		1.1	1.5	V
h _{FE} ⁽¹⁾	DC current gain	$I_C = 0.1 \text{ A}$ $V_{CE} = 5 \text{ V}$ $I_C = 0.8 \text{ A}$ $V_{CE} = 3 \text{ V}$	48 25	75 35	100 50	
t _s	Resistive load Storage time Fall time	$I_C = 2 \text{ A}$ $V_{CC} = 125 \text{ V}$ $I_{B1} = -I_{B2} = 400 \text{ mA}$ $t_p = 300 \mu\text{s}$ $V_{BE(off)} = -5 \text{ V}$		2.4 350	3.5 500	μs ns
E _{ar}	Repetitive avalanche energy	L = 2 mH $C = 1.8 nFV_{BE(off)} = -5 \text{ V}$	6			mJ

^{1.} Pulsed duration = 300 ms, duty cycle $\le .5\%$

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve



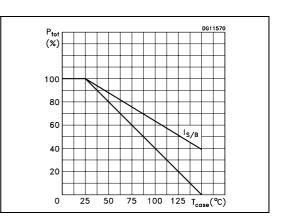
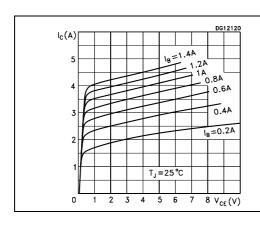


Figure 4. Output characteristics

Figure 5. DC current gain



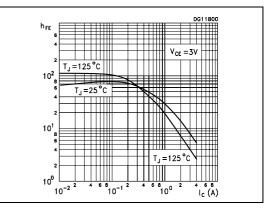
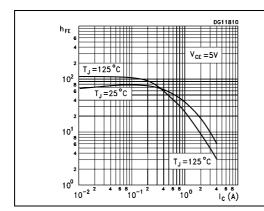
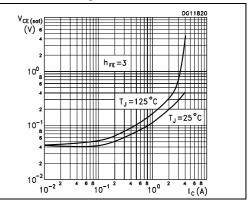


Figure 6. DC current gain

Figure 7. Collector - emitter saturation voltage

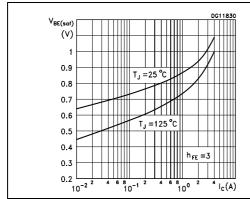




Electrical characteristics BULD742C

Figure 8. Base-emitter saturation voltage

Figure 9. Resistive load switching on times (h_{FE} = 5)



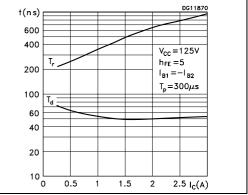
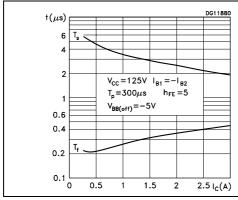


Figure 10. Resistive load switching off times ($h_{FE} = 5$)

Figure 11. Resistive load switching on times (h_{FE} = 10)



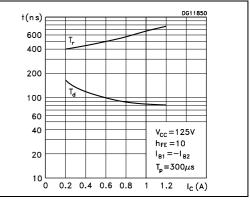
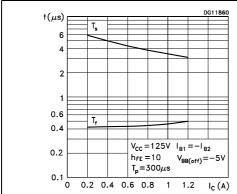
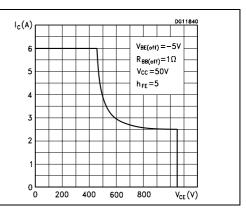


Figure 12. Resistive load switching off Fitimes (h_{FE} = 10)

Figure 13. Reverse biased SOA





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BULD742C Test circuit

3 Test circuit

Figure 14. Energy rating test circuit

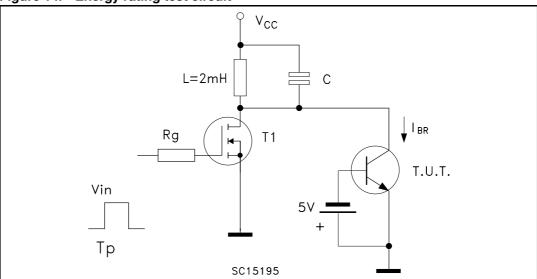
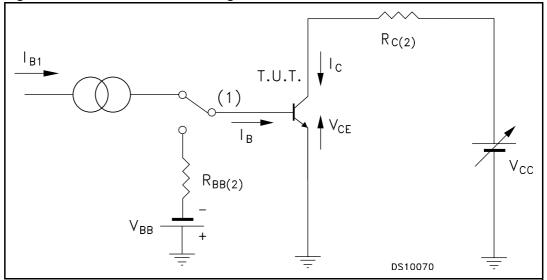


Figure 15. Resistive load switching test circuit



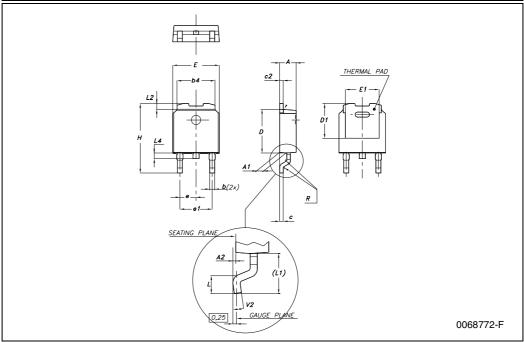
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

DPAK MECHANICAL DATA

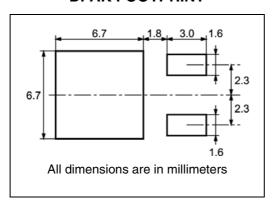
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
е		2.28			0.090	
e1	4.4		4.6	0.173		0.181
Н	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



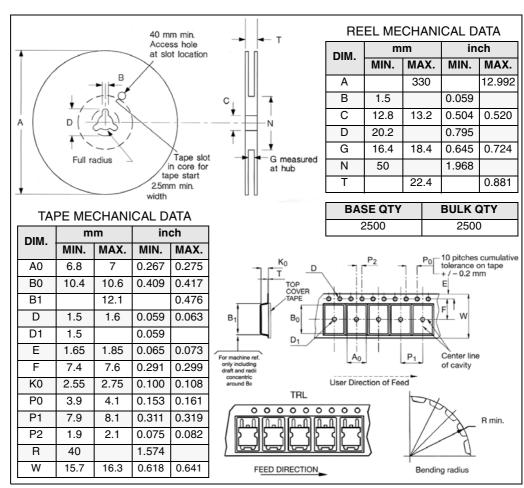
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5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



BULD742C Revision history

6 Revision history

Table 5. Document revision history

	Date	Revision	Changes
Ī	09-Aug-2007	1	First release.

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